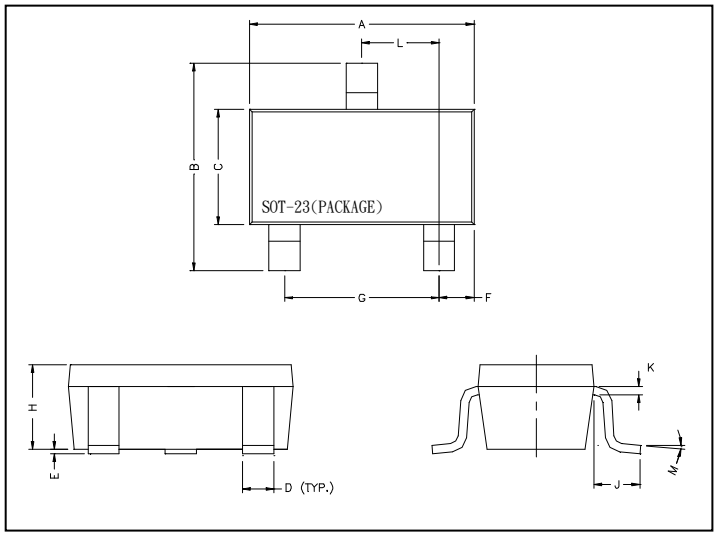
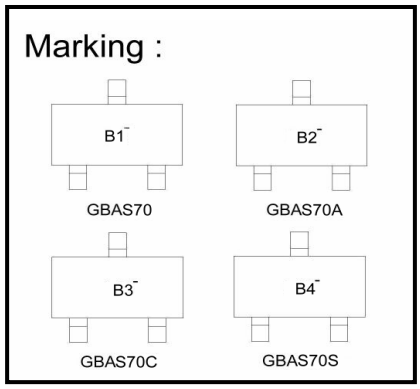
GBAS70/A/C/S

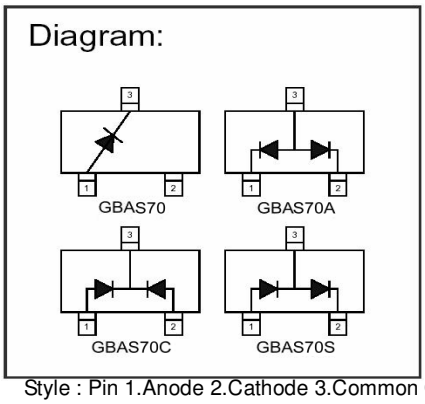
Description

Silicon Schottky Barrier Diodes .

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90 REF.	
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Style : Pin 1.Anode 2.Cathode 3.Common Connection

Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Maximum Operating Temperature Range	Tj	+125	℃
Storage Temperature Range	Tstg	-65 ~ +125	℃
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	70	V
Maximum RMS Voltage	V_{RMS}	49	V
Maximum DC Blocking Voltage	V_{DC}	70	V
Maximum Average Forward Rectified Current	Io	70	mA
Peak Forward Surge Current at 1Sec.	I_{FSM}	100	mA
Typical Junction Capacitane between Terminal(Note 1)	Cj	2.0	pf
Maximum Reverse Recovery Time(Note 2)	T_{RR}	5.0	nSec
Total Power Dissipation at Ta = 25℃	PD	230	mW

Characteristics at Ta = 25℃

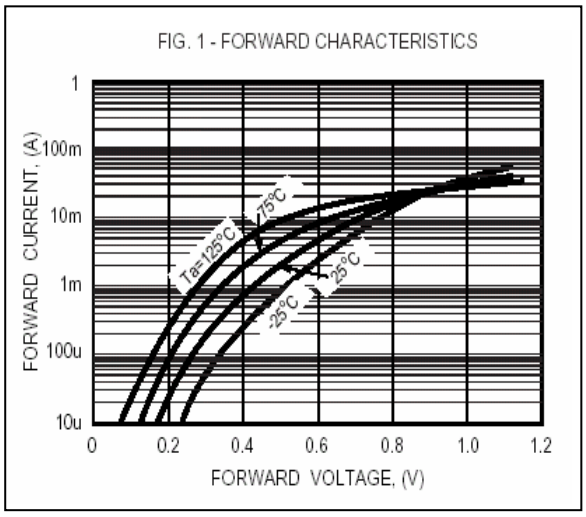
characteristics		Symbol		Unit
Maximum Instantaneous Forward Voltage	@IF=1.0mA	VF	410	mVolts
	@IF=40mA		1000	
Maximum Average Reverse Current at VR=50V		IR	100	nAmps

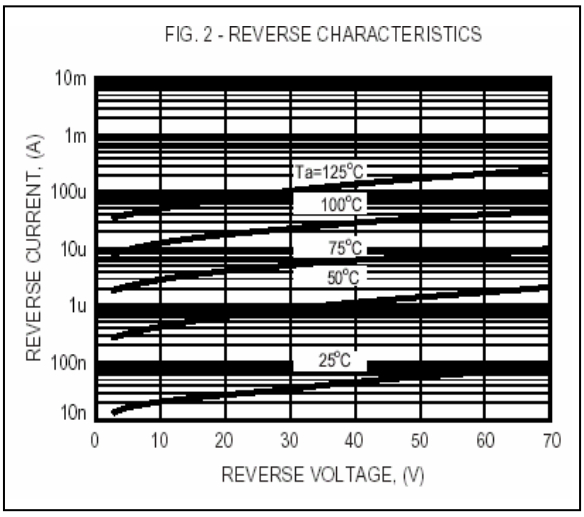
NOTES:1.Measured at 1.0MHz and applied reverse voltage of 0.0 Volts.

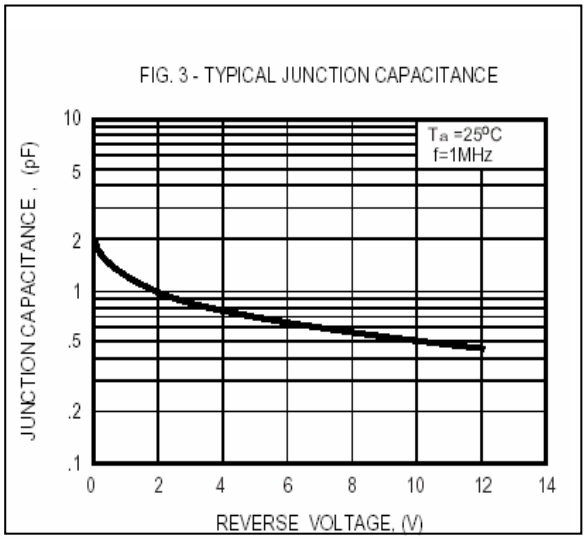
2.Measured at applied forward current of 10mA and reverse current of 10mA.

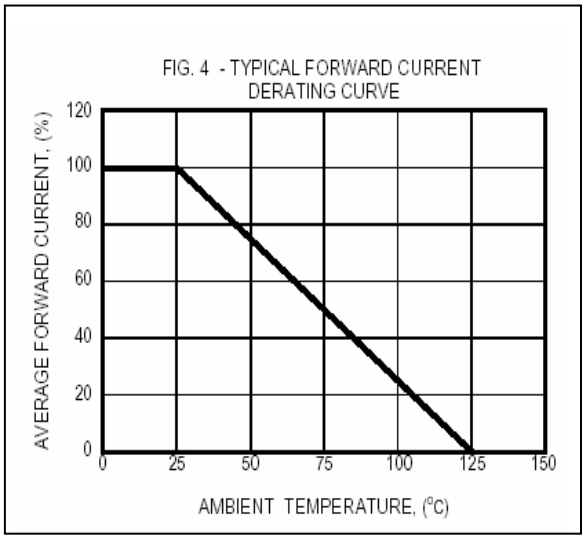
3.ESD sensitive product handling required.

Characteristics Curve









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